

**Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn;** Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266

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**Kropman, Daniel;** Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill

**Stress relaxation mechanism by strain in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn;** Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262

**The complementary use of UV, EPR and SEC to study the structural changes of humic substances during wood waste composting**

Bikovens, O.; **Lepane, Viia; Makarõtševa, Natalja;** Dizhbite, T.; Telysheva, G. Functions of natural organic matter in changing environment 2013 / p. 113-117

**Understanding and control of stress at Si-SiO<sub>2</sub> interface**

Kropman, Daniel; Seeman, Viktor; Medvids, Arturs; Onufrijevs, Pavels; Vitusevich, Svetlana; **Mikli, Valdek** Key engineering materials 2020 / p. 291–296 <https://doi.org/10.4028/www.scientific.net/KEM.850.291> [Journal metrics at Scopus](#) [Article at Scopus](#)